

**1. Scope :**

1-1. This specification applies to N channel silicon MOSFET chips,  
device no. PM-0153

**2. Structure :**

2-1. Planar type .

2-2. Electrodes .

Source : Aluminum alloy .

Gate : Aluminum alloy .

Drain : Gold alloy

**3. Size :**

3-1. Chip size : 70.1 mils x70.1 mils (1.780 mm x1.780 mm ).

3-2. Chip thickness : 12 ±1.5mils ( 0.305± 0.038mm).

3-3. Pad size :

Source : 23.6 mils x 11.8 mils (0.600 mm x 0.300mm ).

Gate : 5.5 mils x 7.1 mils (0.140mm x 0.180 mm ).

3-4. Pattern drawing : Refer to the attached drawing.

**4. Electrical characteristics (Ta = 25 °C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ $I_D = 1mA$	1.5	2.5	3.0	V
Gate to source leakage current	$I_{GSS}$	$V_{GS} = \pm 10V$ $V_{DS} = 0V$			± 1	μA
Drain to source leakage current	$I_{DSS}$	$V_{GS} = 0V$ $V_{DS} = 1500V$			1	μA
Drain to source on resistance	$R_{DS(on)}$	$V_{GS} = 5V$ $I_D = 25mA$		230	500	Ω
Diode forward voltage drop	$V_{SD}$	$V_{GS} = 0V$ $I_{SD} = 25mA$		1.00	1.8	V

Pattern drawing

